PATENT 81788.0026

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of:

Seiichi Mori

Scrial No: 09/456,873

Filed: December 8, 1999

For: NON-VOLATILE SEMICONDUCTOR

MEMORY DEVICE

Art Unit: 2826

Examiner: L. Andujar

I hereby certify that this correspondence is being facsimile transmitted to the United States Patent and Trademark Office, Fax No. (703) spg. 788.2 on line 28. 2001

Sterilog A. Masof Reg. No. 41.179
Narie

June 27, 2001

RESPONSE TO OFFICE ACTION

Assistant Commissioner for Patents Washington, D.C. 20231

Attention: Box Amendment

Dear Sir:

In response to the Office Action mailed March 28, 2001, the three-month statutory period during which to respond thereto expiring June 28, 2001, Applicant submits the following amendments and remarks in the above-identified application.

AMENDMENT

FAX COPY RECEIVED

Please amend the above-identified application as indicated below.

JUN 26 2001

TECHNOLOGY CENTER 2800

IN THE SPECIFICATION:

Please amend the specification as indicated below.

Replace the paragraph starting on page 1, line 19 with the following text:

FIGS. 4A and 48 show sections, taken in two directions orthogonal to each other, of the memory cell structure described above. Normally in a flash memory, the control gate of a